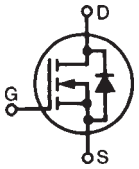
IXYS

Polar™ HiPerFET™ Power MOSFET

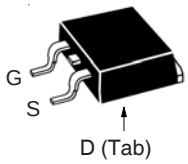
IXFA4N100P
IXFP4N100P

V_{DSS} = 1000V
I_{D25} = 4A
$R_{DS(on)}$ ≤ 3.3Ω

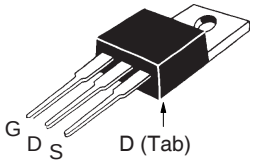
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



TO-263 AA (IXFA)



TO-220AB (IXFP)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	1000	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	1000	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	4	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	8	A
I_A	T_C = 25°C	4	A
E_{AS}	T_C = 25°C	200	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	10	V/ns
P_D	T_C = 25°C	150	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6mm (0.062in.) from Case for 10s	300	°C
T_{sold}	Plastic Body for 10 Seconds	260	°C
F_C	Mounting Force (TO-263)	10.65 / 2.2..14.6	Nm/lb.in.
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	1000			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	3.0		6.0	V
I_{GSS}	V_{GS} = ± 20V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			10	μA
	T_J = 125°C			750	μA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Notes 1			3.3	Ω

Features

- International Standard Packages
- Low $R_{DS(on)}$ and Q_G
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

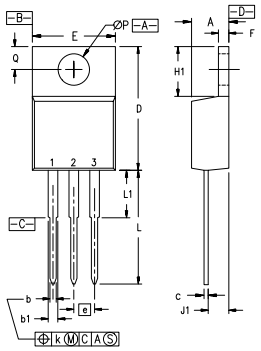
Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS}= 20V, I_D = 0.5 • I_{D25}, Note 1	1.8	3.0		S
R_{Gi}	Gate Input Resistance		1.6		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		1456		pF
C_{oss}			90		pF
C_{rss}			16		pF
$t_{d(on)}$	**Resistive Switching Times**		24		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		36		ns
$t_{d(off)}$	R_G = 5Ω (External)		37		ns
t_f			50		ns
$Q_{g(on)}$	V_{GS}= 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		26		nC
Q_{gs}			9		nC
Q_{gd}			12		nC
R_{thJC}				0.83	°C/W
R_{thCS}	TO-220		0.50		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			4	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			16	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.3	V
t_{rr}	I_F = 2A, V_{GS} = 0V, -di/dt = 100A/μs			300	ns
I_{RM}	V_R = 100V		5.30		A
Q_{RM}			0.34		μC

Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

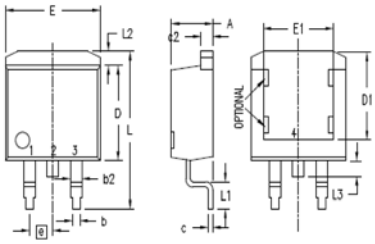
TO-220 (IXFP) Outline

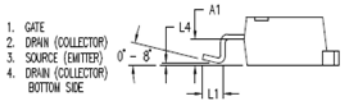


Pins: 1 - Gate 2 - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-263 (IXFA) Outline





SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

Fig. 1. Output Characteristics @ T_J = 25ºC

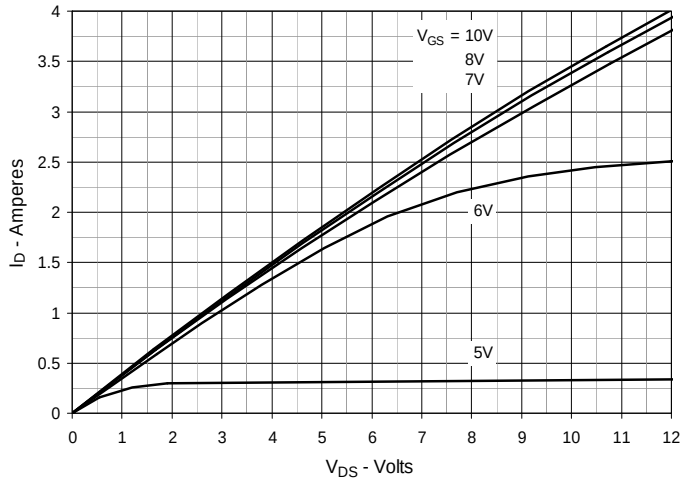


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

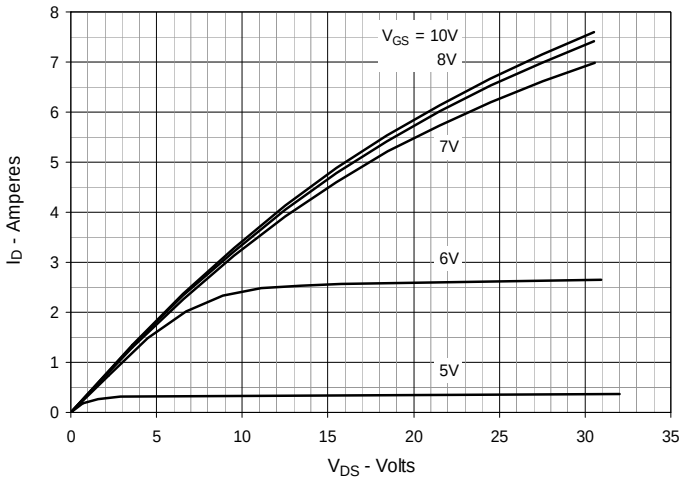


Fig. 3. Output Characteristics @ T_J = 125ºC

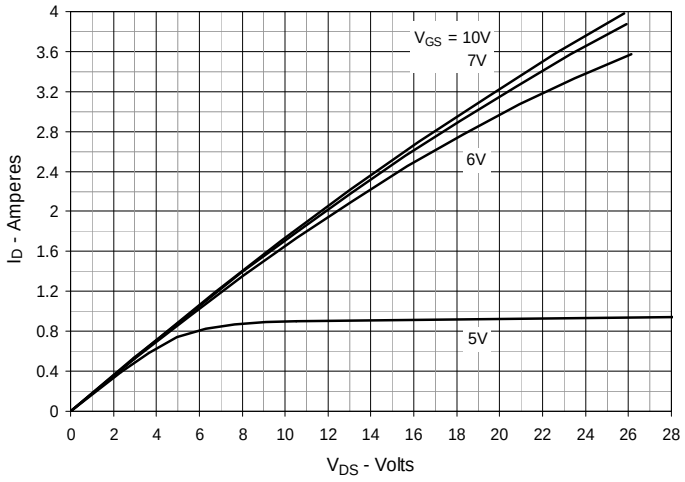


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 2A Value vs. Junction Temperature

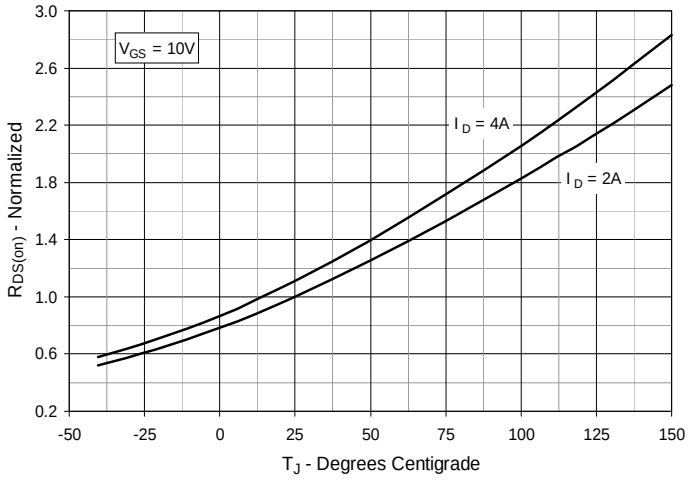


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 2A Value vs. Drain Current

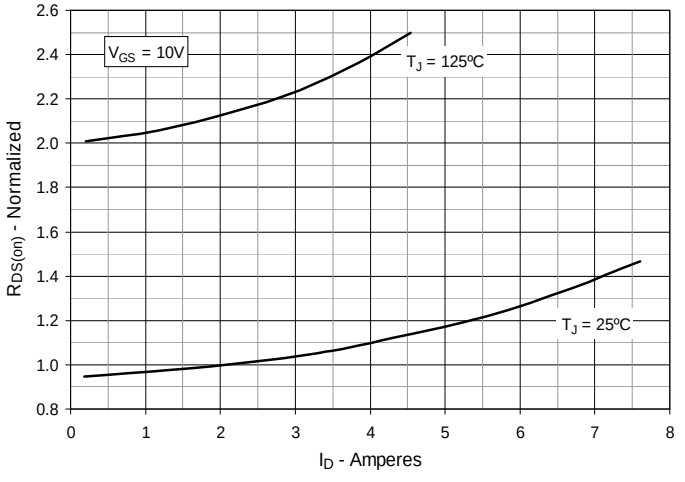


Fig. 6. Maximum Drain Current vs. Case Temperature

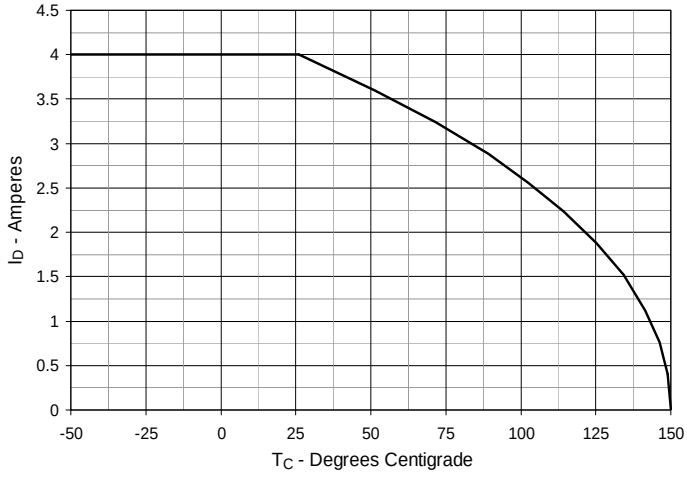


Fig. 7. Input Admittance

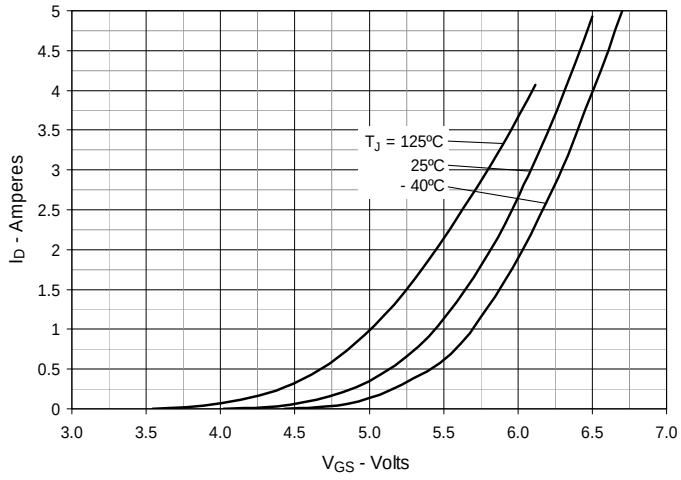


Fig. 8. Transconductance

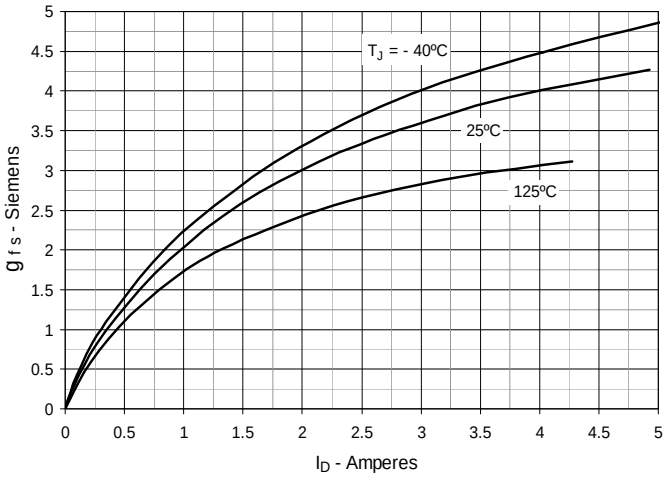


Fig. 9. Forward Voltage Drop of Intrinsic Diode

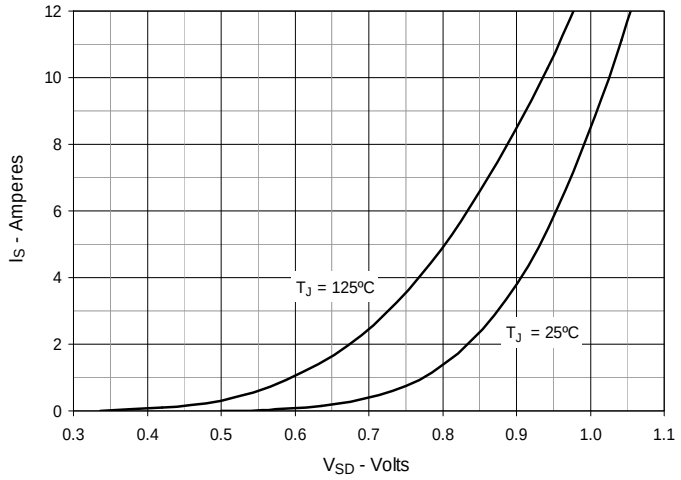


Fig. 10. Gate Charge

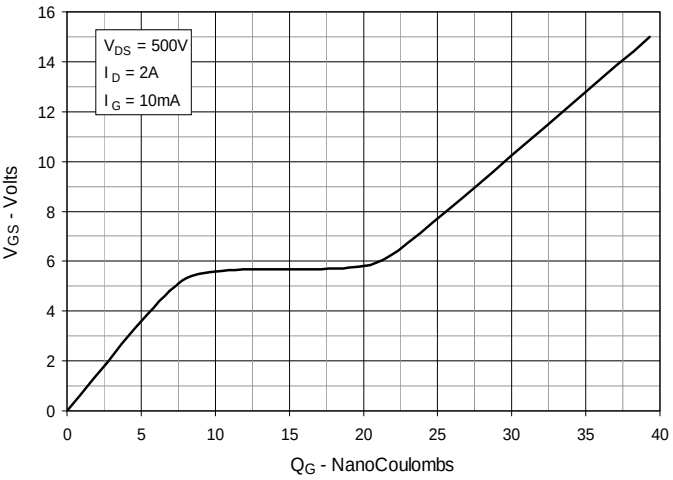


Fig. 11. Capacitance

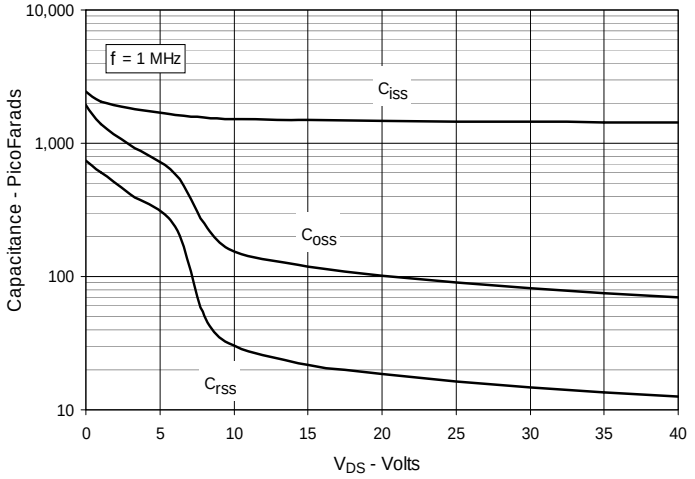
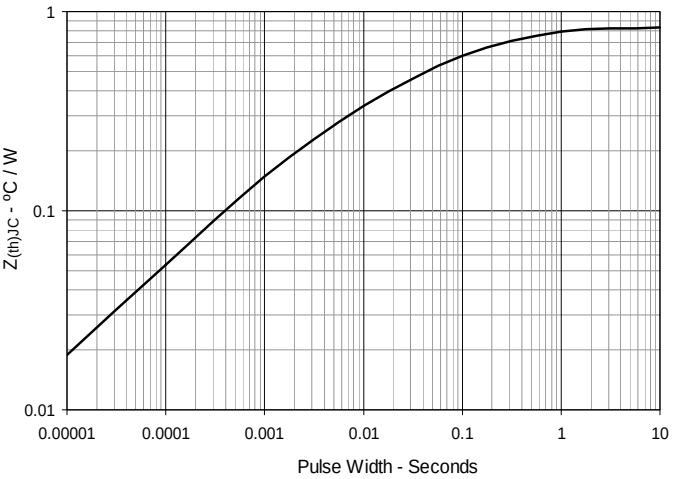


Fig. 12. Maximum Transient Thermal Impedance



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.